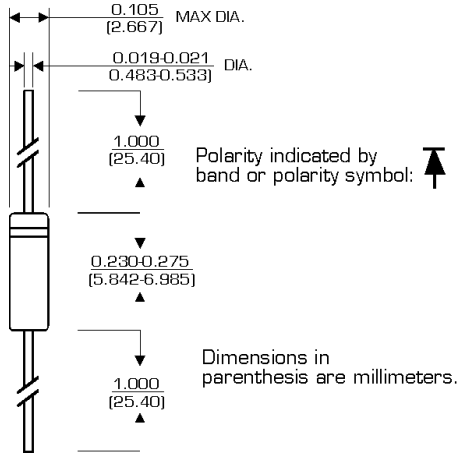
SILICON ZENER DIODE

DESCRIPTION:

The **1N938** is a 9.0 V Silicon Temperature Compensate Zener Diode Designed for General Purpose Voltage Reference Applications.

PACKAGE STYLE DO-7



MAXIMUM RATINGS

I_F	7.5 mA
V_Z	9.0 V
P_{DISS}	500 mW @ T_A = 25 ^{O}C
T_J	-65 ^{O}C to +175 ^{O}C
T_{STG}	-65 ^{O}C to +175 ^{O}C

CHARACTERISTICS T_C = 25 ^{O}C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
V_Z	I_Z = 7.5 mA	8.55		9.45	**V**
ΔV_{ZT}	I_{ZT} = 7.5 mA T_A = -0° C to +75 °C			6.0	**mV**
V_{ZT}	I_{ZT} = 7.5 mA/0.75 mA (AC RMS)			20	**Ohms**
α_{VZ}	I_{ZT} = 7.5 mA	0.001			**%/°C**